## DECLARATION AND POWER OF ATTORNEY FOR PATENT APPLICATION

DOCKET NO. **ESM2000-001** 

As a below named Inventor,

eby declare that:

My residence, post office address and citizenship are as stated below next to my name;

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled Method Of Fabricating A Gate Dielectric Layer For A Thin Film Transistor

the specification of which (check one)
X is attached hereto.
was filed on
Application Serial No.
and was amended on (if applicable)  I hereby state that I have reviewed and understand the course of the last of t
(If applicable)  I hereby state that I have reviewed and understand the contents of the above Identified specification including the claims, as amended by any amendment referred to above.
I acknowledge the duty to disclose information which is material to the examination of this application in accordance with Title 37, Code of Federal Regulations, §1.56(a).
I hereby claim foreign priority benefits under Title 35, United States Code §119 of any foreign application(s) for patent or inventor's certificate listed below and have also identified below any foreign application for patent or inventor's certificate having Prior Foreign Application(s)
(Number) (Country) (Day/Month/Year Filed)
(Number) (Country) (Day/Month/Year Filed)
Thereby claim the benefit under Title 35, United States Code §120 of any United States application(s) listed below and, insofar provided by the first paragraph of Title 35, United States Code, §112, I acknowledge the duty to disclose material information as anational or PCT international filing date of this application:
(Application Serial No.) (Filing Date) (Status) (patented, pending, abandoned)
Thereby declare that all statements made herein of my own knowledge are true and that all statements made on information and the like are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.
POWER OF ATTORNEY: As a named inventor, I hereby appoint the following attorney(s) and/or agent(s) to prosecute this application and transact all business in the Patent and Trademark Office connected therewith. (list name & registration no.) GEORGE 0. SAILE. (Reg. No. 19,572), STEPHEN B. ACKERMAN (Reg. No. 37,761)
Send Correspondence to: 20 MCINTOSH DRIVE, POUGHKEEPSIE; NEW YORK 12603  Direct telephone Calls to: (name & telephone number) GEORGE 0. SAILE NEW YORK 914 452 5863
Full name of sole or first inventor  RICHARO BULLOCK  Date  22/12/00
Residence Rullock
Citizenship  (UK) United Kingdom  10, BARNFIELD, RIVERSIDE PARK, PONTHIR
10, BARNFIELD, RIVERSIDE PARK, PONTHIR
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Inventor's signature	<del></del> :	· · · · · · · · · · · · · · · · · · ·			
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